

# **WLL Transmit Upconverter IC for 3.5GHz**

- Fully Integrated IF Variable Gain Amplifier, Mixer, LO-Buffer, three RF Amplifier Stages and a switched Attenuator
- High Conversion Gain: typ. 29 dB
- Gain Control Range: >75 dB
- 1dB-Compression Point P<sub>1dB</sub>: +17,0 dBm
- Output 3<sup>rd</sup> Order Intercept Point (OIP3) at G<sub>max</sub>: +28 dBm
- Very low LO-Power demand of typ. -5 to 0 dBm
- · Minimum of external components and easy matching
- Total Current Consumption: typ. 270mA @ 5V
- Temperature Range: -40°C to +85°C

ESD: Electrostatic discharge sensitive device Observe handling Precautions!



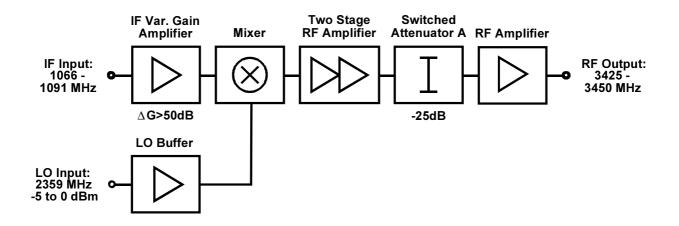
Туре	Marking	Ordering code (tape and reel)	Package
CGY340	CGY340	Q62702G81	MW-16

Maximum Ratings	Port	Symbol	Value		Unit
			min	max	
Positive Supply Voltage	3, 5, 6, 11, 12	V <sub>DLO</sub> , V <sub>DRF1</sub> , V <sub>DRF3</sub> , V <sub>DRF2</sub> , V <sub>DVGA</sub>	0	+8	V
Negative Supply Voltage	13	V <sub>G</sub>	0	-6	V
IF VGA Control Voltage	14	VGA	-2.0	+8	V
Voltage at Step Attenuator	9, 10	A, A bar	-0.5	+8	V
Power into IF Input	16	IF		10	dBm
Power into LO Input	1	LO		10	dBm
Channel Temperature		T <sub>Ch</sub>		150	°C
Storage Temperature		T <sub>stg</sub>	-55	150	°C

Thermal Resistance			
Channel to Soldering Point (GND)	R <sub>thChS</sub>	T.b.d.	K/W



## **RF Block Diagram**



#### **Electrical Characteristics**

<u>Test conditions:</u>  $T_a$  = 25°C;  $V_{DD}$  = 5V,  $V_{GG}$  = -5V;  $f_{IF}$  = 1066-1091 MHz;  $P_{IF}$  = -20 dBm;  $f_{LO}$  = 2359 MHz;  $P_{LO}$  = 0 dBm;  $f_{RF}$  = 3425-3450 MHz, VGA adjusted to max. gain, attenuator A "OUT" or "IN" (for further information about the VGA and the attenuator see "Attenuator State" on page 5).:

Parameter, Test Conditions	Symbol	min	typ	max	Unit
Operating Drain Current	I <sub>op</sub>	-	270	-	mA
Operating Drain Current LO Buffer only	I <sub>LO</sub>	-	10	-	mA
Operating Gate Current	l <sub>g</sub>	_	1.3	-	mA

<u>Test conditions:</u> As above, but VGA adjusted to max. gain and attenuator A "OUT" (for further information about the VGA and the attenuator see "Attenuator State" on page 5).

Parameter, Test Conditions	Symbol	min	typ	max	Unit
Conversion Gain	Gc	-	29,0	-	dB
Total Dynamic Range Output Power 1)	$\Delta G_{tot}$	-	>75	-	dB
VGA Dynamic Range Output Power	$\Delta G_{VGA}$	-	>50	-	dB
SSB Noise Figure	F <sub>ssb</sub>	-	5,5	-	dB
1dB-Compression Point	P <sub>1dB</sub>	-	17,0	-	dBm
Output 3 <sup>rd</sup> Order Intercept Point (OIP3) at G <sub>max</sub>	OIP3	-	+28	-	dBm



Signal Breakthrough at $P_{LO}$ = 0 dBm and $P_{RF}$ = +8.5 dBm:					
LO Leakage at RF-Port	P <sub>LO</sub>	-	-38	-	dBm
LO Leakage at IF-Port	P <sub>LO</sub>	-	-31	-	dBm
Spectral Regrowth at $G_{max}$ and $P_{out} = +8.5 \text{ dBm}$ :					
Offset: ±256kHz		-	-46	-	dBc
Offset: ±512kHz		-	-66	-	dBc
Offset: ±768kHz		-	>-70	-	dBc
Return Loss:					
IF Port 3)	S <sub>11</sub>	-	14	-	dB
RF Port 3)	S <sub>22</sub>	-	10	-	dB
LO Port <sup>3)</sup>	S <sub>11</sub>	-	20	-	dB

Note 1: Variable Gain Amplifier (VGA) and Switched Attenuator A

Note 2: Modulation: π/4 DQPSK (2b/sym). Symbol Rate: 256ksym/s. Mode: PHS. Filter: RNYQ. Filter Alpha: 0.40.

Note 3: Configuration as shown on application board

<u>Test conditions:</u> As above, but VGA adjusted to max. gain and attenuator A "IN" (for further information about the VGA and the attenuator see "Attenuator State" on page 5).

Parameter, Test Conditions	Symbol	min	typ	max	Unit
Conversion Gain	Gc	-	3,0	-	dB

<u>Test conditions:</u> As above, but VGA adjusted to min. gain and attenuator A "OUT" (for further information about the VGA and the attenuator see "Attenuator State" on page 5).

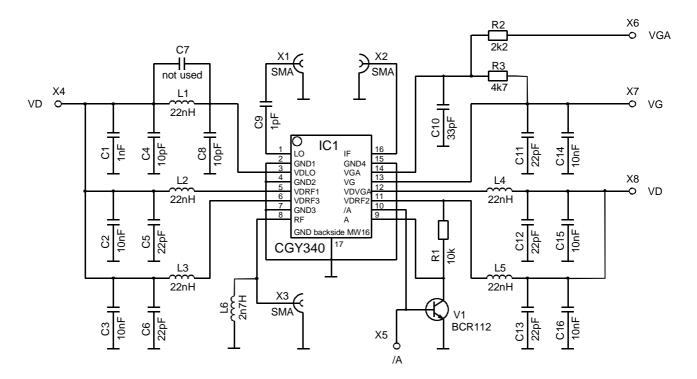
Parameter, Test Conditions	Symbol	min	typ	max	Unit
Conversion Gain	Gc	-	<-29,0	-	dB

<u>Test conditions:</u> As above, but VGA adjusted to min. gain and attenuator A "IN" (for further information about the VGA and the attenuator see "Attenuator State" on page 5).

Parameter, Test Conditions	Symbol	min	typ	max	Unit
Conversion Gain	Gc	-	<-50,0	-	dB



## **Application Circuit**



Notes: Package of all resistors and capacitors: 0603.

All inductors: TOKO LL-1608-FH.

The attenuator A is "OUT" without supplying port A, the gain of the variable gain amplifier is maximum when X6 (VGA) is supplied with +5.0V (for further information about the VGA and the attenuator see "Attenuator State" on page 5).



#### **Pin Definitions and Functions**

Pin No.	Symbol	Function	Bias Voltage
1	LO	LO Input	
2	GND1	GND	0V
3	VDLO	Mixer Drain Bias	+5V
4	GND2	GND	0V
5	VDRF1	1 <sup>st</sup> RF Amp Drain Bias	+5V
6	VDRF3	3 <sup>rd</sup> RF Amp Drain Bias	+5V
7	GND3	GND	0V
8	8 RF RF Output		
9	A Attenuator Control		+5V, 0V
10	A bar	Attenuator Control bar	0V, +5V
11	VDRF2	2 <sup>nd</sup> RF Amp Drain Bias	+5V
12	VDVGA	IF VGA Drain Bias	+5V
13	VG	Negative Supply	-5V
14	VGA	IF VGA Control Voltage	-1.6V to +1.8V 1)
15	GND4	GND	0V
16	IF	IF Input	
MW16 Heatsink Slug	GND	OWP Ground	0V

Note 1: A voltage of -1.6V to +1.8V on Pin 14 is equal to a voltage of 0V to +5V on pad X6 of the application circuit.

#### **Attenuator State**

Attenuator A "IN" Pin 9 = Low, Pin 10 = High

"OUT" Pin 9 = High, Pin 10 = Low

Logic level High:  $V_{High} > V_D - 0.15V$ Logic level Low:  $V_{Low} < +0.5V$ 

Note: Attenuator "OUT" is defined as maximum gain state.

Attenuator "IN" is defined as minimum gain state.

VGA Min. Gain Pin 14 = -1.5V (equal to a voltage of 0V on pad X6 of the

application circuit)

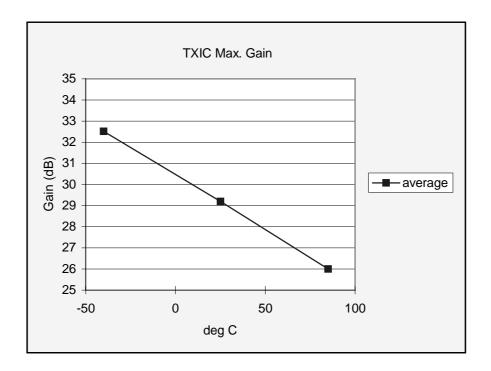
Max. Gain Pin 14 = +1.8V (equal to a voltage of 5V on pad X6 of the

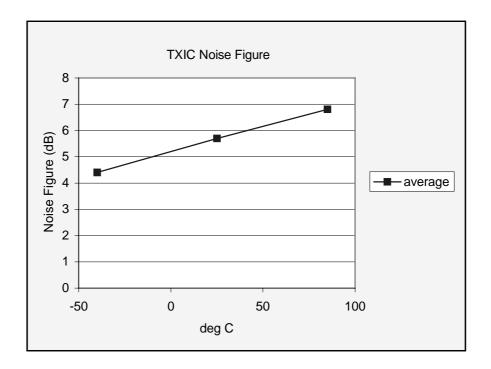
application circuit)



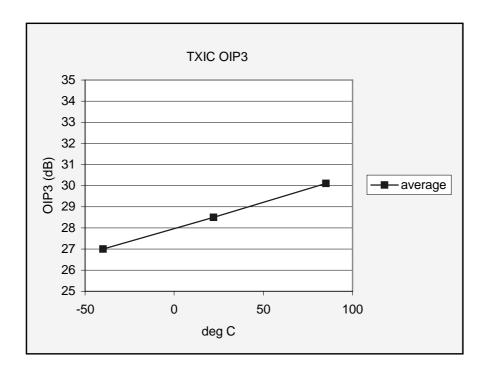
## **Electrical Characteristics versus Temperature**

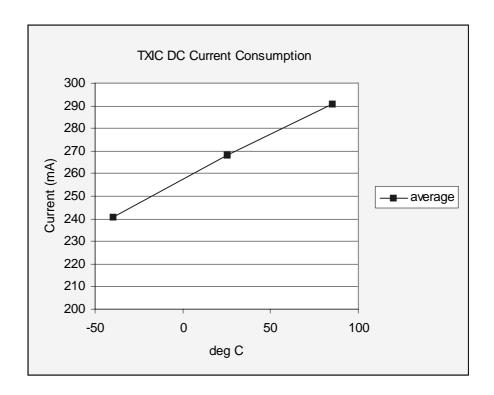
**Test conditions:**  $V_{\rm DD} = 5$ V,  $V_{\rm GG} = -5$ V;  $f_{\rm IF} = 1066-1091$  MHz;  $P_{\rm IF} = -20$  dBm;  $f_{\rm LO} = 2359$  MHz;  $P_{\rm LO} = 0$  dBm;  $f_{\rm RF} = 3425-3450$  MHz, VGA adjusted to max. gain and attenuator A "OUT" (for further information about the VGA and the attenuator see "Attenuator State" on page 5).





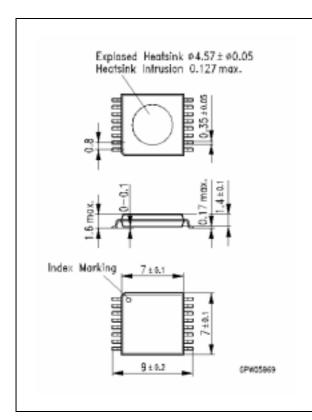








### **Semiconductor Device Layout MW16**



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